

AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1 – 9. (Canceled)

10. (Original) A semiconductor device comprising:

a first hydrogen barrier film having an oxidized region in a surface thereof;

a capacitor device formed on the first hydrogen barrier film; and

a second hydrogen barrier film which contains oxygen and which is formed to cover the capacitor device,

wherein the first and second hydrogen barrier films adhere to each other by oxygen bonding while the oxidized region located around the perimeter of the capacitor device is interposed therebetween.

11. (Original) A semiconductor device comprising:

a first hydrogen barrier film having a nitrided region in a surface thereof;

a capacitor device formed on the first hydrogen barrier film; and

a second hydrogen barrier film which contains nitrogen and which is formed to cover the capacitor device,

wherein the first and second hydrogen barrier films adhere to each other by nitrogen bonding while the nitrified region located around the perimeter of the capacitor device is interposed therebetween.

12. (Currently Amended) The semiconductor device of claim [[6,]] 10[[,]] or 11, wherein the first and second hydrogen barrier films adhere to each other so that no silicon oxide film is interposed between the first and second hydrogen barrier films.

13. (Currently Amended) The semiconductor device of claim [[6,]] 10[[,]] or 11, wherein the first and second hydrogen barrier films are films made of the same material.

14. (Currently Amended) The semiconductor device of claim [[6,]] 10[[,]] or 11, wherein the capacitor device comprises a lower electrode formed above the first hydrogen barrier film, a capacitor insulating film formed on the lower electrode, and an upper electrode formed on the capacitor insulating film, and

the capacitor insulating film is made of a ferroelectric film or a high dielectric film.

15. (Original) The semiconductor device of claim 14, wherein the capacitor insulating film is made of $\text{SrBi}_2(\text{Ta}_x\text{Nb}_{1-x})_2\text{O}_9$, $\text{Pb}(\text{Zr}_x\text{Ti}_{1-x})\text{O}_3$, $(\text{Ba}_x\text{Sr}_{1-x})\text{TiO}_3$, $(\text{Bi}_x\text{La}_{1-x})_4\text{Ti}_3\text{O}_{12}$ (where x satisfies $0 \leq x \leq 1$ in the above chemical formulas), or Ta_2O_5 .

16 - 38. (Canceled)